# General purpose (dual digital transistors) UMD6N / IMD6A

### Features

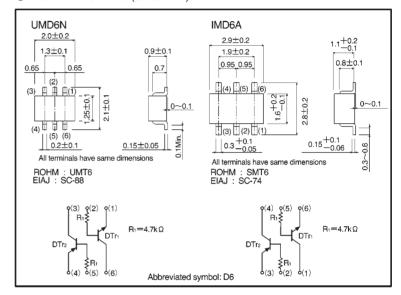
- Both the DTA143T chip and DTC143T chip in a UMT or SMT package.
- Mounting possible with UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

### Structure

A PNP and a NPN digital transistor (each with a single built in resistor)

The following characteristics apply to both DTr<sub>1</sub> and DTr<sub>2</sub>, however, the "–" sign on DTr<sub>2</sub> values for the PNP type have been omitted.

# External dimensions (Units: mm)



### ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	50	V	
Collector-emitter voltage		Vceo	50	V	
Emitter-base voltage		Vево	5	V	
Collector current		Ic	100	mA	
Collector power dissipation	UMD6N	Pc Pc	150 (TOTAL)	*1 mW	
	IMD6A	FC	300 (TOTAL)	*2	
Junction temperature		Tj	150	్డ	
Storage temperature		Tstg	-55~+150	°C	

<sup>\*1 120</sup>mW per element must not be exceeded.



<sup>\*2 200</sup>mW per element must not be exceeded.

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## • Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	50	_	_	٧	Ic=50 μ A
Collector-emitter breakdown voltage	BVCEO	50	_	_	٧	Ic=1mA
Emitter-base breakdown voltage	ВУЕВО	5	_	_	٧	I <sub>E</sub> =50 μ A
Collector cutoff current	Ісво	_	_	0.5	μΑ	V <sub>CB</sub> =50V
Emitter cutoff current	Івю	_	_	0.5	μΑ	V <sub>EB</sub> =4V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	_	_	0.3	٧	Ic/I <sub>B</sub> =5mA/0.25mA
DC current transfer ratio	hfe	100	250	600	_	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA
Transition frequency	fτ	_	250	_	MHz	Vc=10mA, I=-5mA, f=100MHz *
Input resistance	R <sub>1</sub>	3.29	4.7	6.11	kΩ	_

<sup>\*</sup> Transition frequency of the transistor

### Packaging specifications

	Packaging type	Taping		
	Code	TR	T108	
Part No.	Basic ordering unit (pieces)	3000	3000	
UMD6N		0	_	
IMD6A		_	0	

# Electrical characteristic curvesDTr<sub>1</sub> (NPN)

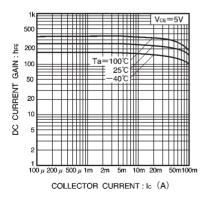


Fig.1 DC current gain vs. collector current

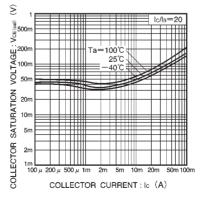


Fig.2 Collector-emitter saturation voltage vs. collector current

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DTr<sub>2</sub> (PNP)

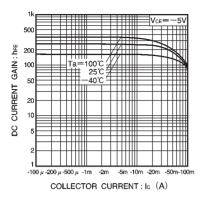


Fig.3 DC current gain vs. collector current

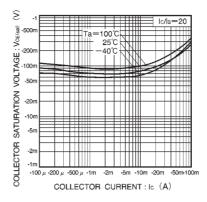


Fig.4 Collector-emitter saturation voltage vs. collector current